

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)
Shunpei YAMAZAKI et al.)
Serial No. 09/352,362)
Filed: July 13, 1999)
For: CRYSTALLINE SEMICONDUCTOR)
THIN FILM, METHOD OF)
FABRICATING THE SAME,)
SEMICONDUCTOR DEVICE, AND)
METHOD OF FABRICATING THE)
SAME)

Group Art Unit: 2815

Examiner: E. ORTIZ



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Charles D. Caldwell

AMENDMENT AND RESPONSE TO RESTRICTION REQUIREMENT

Commissioner for Patents
Washington, D.C. 20231

08/10/2000 JADD01 00000074 09352362

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18.00 CP

Sir:

In response to the Office Action of July 5, 2000, please amend the subject application as follows:

IN THE CLAIMS:

Cancel claims 1-4 without prejudice to applicant('s') right to file a divisional application with respect thereto.

Please add the following new claims:

--25. A method of fabricating a semiconductor device including a thin film transistor, wherein the thin film transistor is formed through the steps of:

adding a catalytic element for facilitating crystallization of an amorphous semiconductor thin film to a part or an entire region of the amorphous semiconductor thin film;

carrying out a first heat treatment to transform the part or the entire region of the amorphous semiconductor thin film into a crystalline semiconductor thin film;

selectively providing the crystalline semiconductor thin film with an element of group 15;

carrying out a second heat treatment to getter the catalytic element into a region of the crystalline semiconductor thin film selectively provided with the element of group 15;

patterning the crystalline semiconductor thin film into at least one crystalline semiconductor island to become at least a channel formation region by removing at least the region of the crystalline

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Shunpei YAMAZAKI et al.

Serial No. 09/352,362

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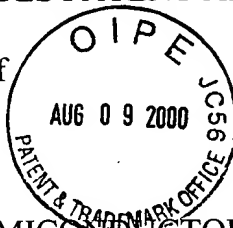
For: CRYSTALLINE SEMICONDUCTOR

THIN FILM, METHOD OF FABRICATING

THE SAME, SEMICONDUCTOR DEVICE,

AND METHOD OF FABRICATING THE

SAME



) Examiner: E. ORTIZ

) Group Art Unit: 2815

CERTIFICATE OF MAILING

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Phyllis O'Connell

Commissioner for Patents

Washington, D.C. 20231

Sir:

Transmitted herewith is an Amendment and Response to Restriction Requirement in the above-identified application.

The fee has been calculated as shown below:

	Claims Remaining After Amendment		Highest Number Previously Paid For	Present Extra	Small/Large Entity Rate	Fee
Total	25	Minus	24	1	x \$9/\$18	\$ 18.00
Indep.	12	Minus	12	-0-	x \$39/\$78	\$0.00
First Presentation of Multiple Dependent Claim					+ \$130/\$260	\$0.00
TOTAL						\$18.00

[X] A check in the amount of \$18.00 to cover the additional claims is enclosed.

[X] In the event applicant(s) has overlooked the need for any petition and fee for extension of time, and such extension is required, applicant(s) requests that this be considered a petition therefor and that such fee be charged to Deposit Account No. 19-2380.

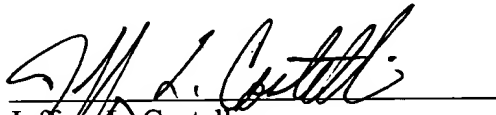
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- [X] The Commissioner is hereby authorized to charge fees under 37 CFR 1.16, 1.17 (except the Issue Fee) which may be required now or hereafter, or credit any overpayment, to Deposit Account No. 19-2380. A duplicate copy of this sheet is attached.

Respectfully submitted,



Jeffrey L. Costellia
Reg. No. 35,483

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EJR/JLC/wks

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